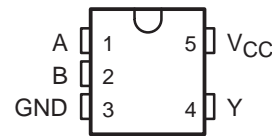


SN74LVC1G00 SINGLE 2-INPUT POSITIVE-NAND GATE

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- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **I_{off} Feature Supports Partial-Power-Down Mode Operation**
- **Supports 5-V V_{CC} Operation**
- **Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages**

DBV OR DCK PACKAGE
(TOP VIEW)



description

This single 2-input positive-NAND gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G00 performs the Boolean function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC1G00 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

| INPUTS | | OUTPUT |
|--------|---|--------|
| A | B | Y |
| H | H | L |
| L | X | H |
| X | L | H |

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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**TEXAS
INSTRUMENTS**

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PRODUCT PREVIEW

SN74LVC1G00

SINGLE 2-INPUT POSITIVE-NAND GATE

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

| | |
|--|----------------------------|
| Supply voltage range, V_{CC} | –0.5 V to 6.5 V |
| Input voltage range, V_I (see Note 1) | –0.5 V to 6.5 V |
| Output voltage range, V_O (see Notes 1 and 2) | –0.5 V to $V_{CC} + 0.5$ V |
| Input clamp current, I_{IK} ($V_I < 0$) | –50 mA |
| Output clamp current, I_{OK} ($V_O < 0$) | –50 mA |
| Continuous output current, I_O | ±50 mA |
| Continuous current through V_{CC} or GND | ±100 mA |
| Package thermal impedance, θ_{JA} (see Note 3): DBV package | 347°C/W |
| DCK package | 389°C/W |
| Storage temperature range, T_{stg} | –65°C to 150°C |

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 2. The value of V_{CC} is provided in the recommended operating conditions table.
 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

| | | MIN | MAX | UNIT | |
|---------------------|------------------------------------|--|----------------------|----------------------|------|
| V_{CC} | Supply voltage | Operating | 1.65 | 5.5 | V |
| | | Data retention only | 1.5 | | |
| V_{IH} | High-level input voltage | $V_{CC} = 1.65$ V to 1.95 V | $0.65 \times V_{CC}$ | | V |
| | | $V_{CC} = 2.3$ V to 2.7 V | 1.7 | | |
| | | $V_{CC} = 3$ V to 3.6 V | 2 | | |
| | | $V_{CC} = 4.5$ V to 5.5 V | $0.7 \times V_{CC}$ | | |
| V_{IL} | Low-level input voltage | $V_{CC} = 1.65$ V to 1.95 V | | $0.35 \times V_{CC}$ | V |
| | | $V_{CC} = 2.3$ V to 2.7 V | | 0.7 | |
| | | $V_{CC} = 3$ V to 3.6 V | | 0.8 | |
| | | $V_{CC} = 4.5$ V to 5.5 V | | $0.3 \times V_{CC}$ | |
| V_I | Input voltage | 0 | 5.5 | V | |
| V_O | Output voltage | 0 | V_{CC} | V | |
| I_{OH} | High-level output current | $V_{CC} = 1.65$ V | | –4 | mA |
| | | $V_{CC} = 2.3$ V | | –8 | |
| | | $V_{CC} = 3$ V | | –16 | |
| | | $V_{CC} = 4.5$ V | | –24 | |
| I_{OL} | Low-level output current | $V_{CC} = 1.65$ V | | 4 | mA |
| | | $V_{CC} = 2.3$ V | | 8 | |
| | | $V_{CC} = 3$ V | | 16 | |
| | | $V_{CC} = 4.5$ V | | 24 | |
| $\Delta t/\Delta v$ | Input transition rise or fall rate | $V_{CC} = 1.8$ V ± 0.15 V, 2.5 V ± 0.2 V | | 20 | ns/V |
| | | $V_{CC} = 3.3$ V ± 0.3 V | | 10 | |
| | | $V_{CC} = 5$ V ± 0.5 V | | 5 | |
| T_A | Operating free-air temperature | –40 | 85 | °C | |

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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SINGLE 2-INPUT POSITIVE-NAND GATE

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | V _{CC} | MIN | TYP† | MAX | UNIT |
|------------------|---------------|--|-----------------|----------------------|------|------|------|
| V _{OH} | | I _{OH} = -100 μA | 1.65 V to 5.5 V | V _{CC} -0.1 | | | V |
| | | I _{OH} = -4 mA | 1.65 V | 1.2 | | | |
| | | I _{OH} = -8 mA | 2.3 V | 1.9 | | | |
| | | I _{OH} = -16 mA | 3 V | 2.4 | | | |
| | | I _{OH} = -24 mA | | 2.3 | | | |
| | | I _{OH} = -32 mA | 4.5 V | 3.8 | | | |
| V _{OL} | | I _{OL} = 100 μA | 1.65 V to 5.5 V | | | 0.1 | V |
| | | I _{OL} = 4 mA | 1.65 V | | | 0.45 | |
| | | I _{OL} = 8 mA | 2.3 V | | | 0.3 | |
| | | I _{OL} = 16 mA | 3 V | | | 0.4 | |
| | | I _{OL} = 24 mA | | | | 0.55 | |
| | | I _{OL} = 32 mA | 4.5 V | | | 0.55 | |
| I _I | A or B inputs | V _I = 5.5 V or GND | 0 to 5.5 V | | | ±5 | μA |
| I _{off} | | V _I or V _O = 5.5 V | 0 | | | ±10 | μA |
| I _{CC} | | V _I = 5.5 V or GND, I _O = 0 | 1.65 V to 5.5 V | | | 10 | μA |
| ΔI _{CC} | | One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND | 3 V to 5.5 V | | | 500 | μA |
| C _i | | V _I = V _{CC} or GND | 3.3 V | | | | pF |

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | V _{CC} = 1.8 V ± 0.15 V | | V _{CC} = 2.5 V ± 0.2 V | | V _{CC} = 3.3 V ± 0.3 V | | V _{CC} = 5 V ± 0.5 V | | UNIT |
|-----------------|--------------|-------------|----------------------------------|-----|---------------------------------|-----|---------------------------------|-----|-------------------------------|-----|------|
| | | | MIN | MAX | MIN | MAX | MIN | MAX | MIN | MAX | |
| t _{pd} | A or B | Y | | | | | | | | | ns |

operating characteristics, T_A = 25°C

| PARAMETER | | TEST CONDITIONS | V _{CC} = 1.8 V | V _{CC} = 2.5 V | V _{CC} = 3.3 V | V _{CC} = 5 V | UNIT |
|-----------------|-------------------------------|-----------------|-------------------------|-------------------------|-------------------------|-----------------------|------|
| | | | TYP | TYP | TYP | TYP | |
| C _{pd} | Power dissipation capacitance | f = 10 MHz | | | | | pF |

PRODUCT PREVIEW



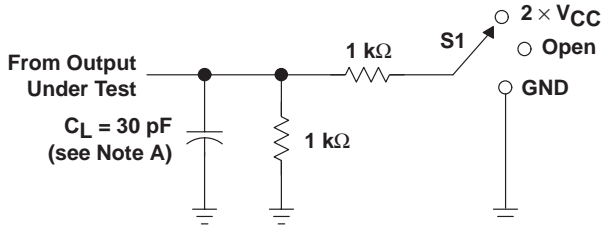
SN74LVC1G00

SINGLE 2-INPUT POSITIVE-NAND GATE

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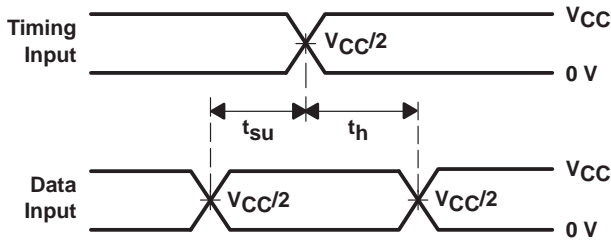
PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$$

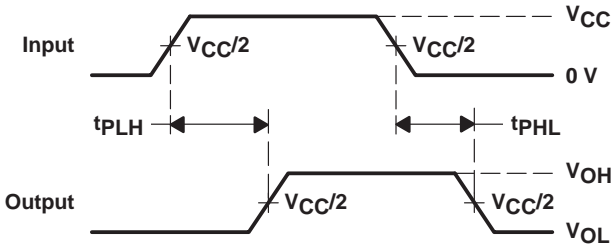


LOAD CIRCUIT

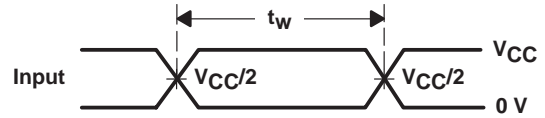
| TEST | S1 |
|-------------------|-------------------|
| t_{pd} | Open |
| t_{PLZ}/t_{PZL} | $2 \times V_{CC}$ |
| t_{PHZ}/t_{PZH} | GND |



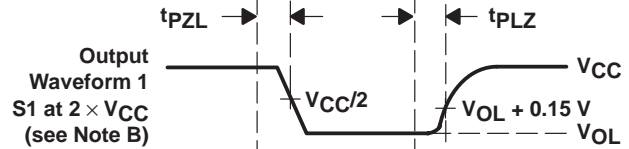
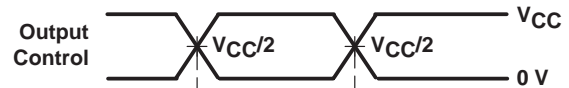
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



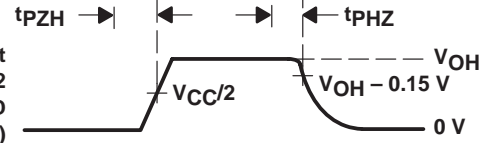
VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



Output Waveform 1
S1 at $2 \times V_{CC}$
(see Note B)



Output Waveform 2
S1 at GND
(see Note B)

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

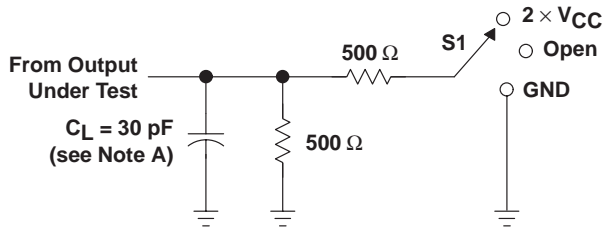
- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

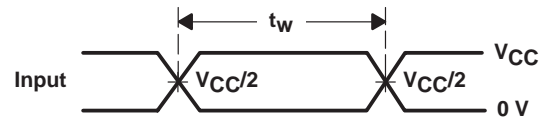
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

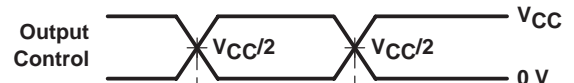
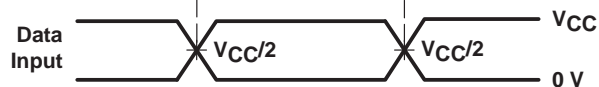


LOAD CIRCUIT

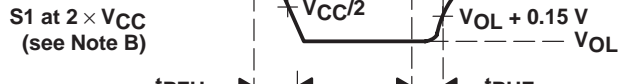
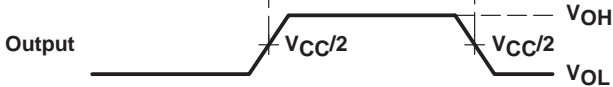
| TEST | S1 |
|-------------------|---------------------|
| t_{pd} | Open |
| t_{PLZ}/t_{PZL} | 2 \times V_{CC} |
| t_{PHZ}/t_{PZH} | GND |



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

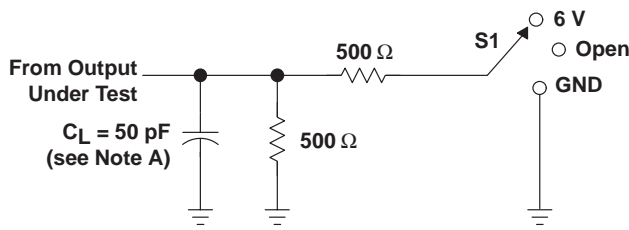
PRODUCT PREVIEW

SN74LVC1G00 SINGLE 2-INPUT POSITIVE-NAND GATE

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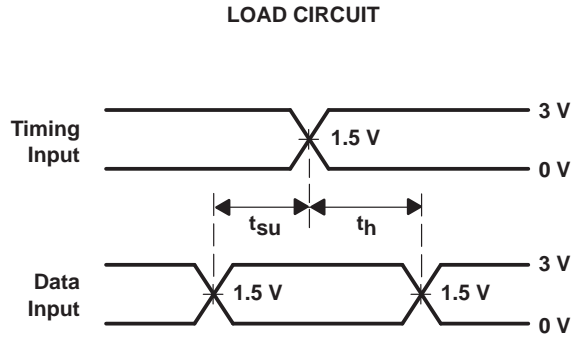
PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$$

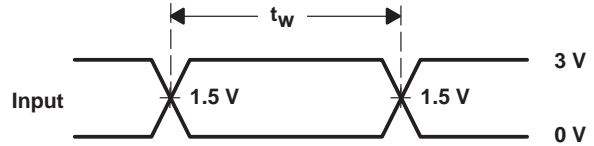


LOAD CIRCUIT

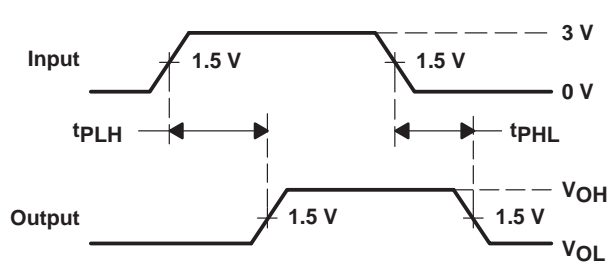
| TEST | S1 |
|-------------------|------|
| t_{pd} | Open |
| t_{PLZ}/t_{PZL} | 6 V |
| t_{PHZ}/t_{PZH} | GND |



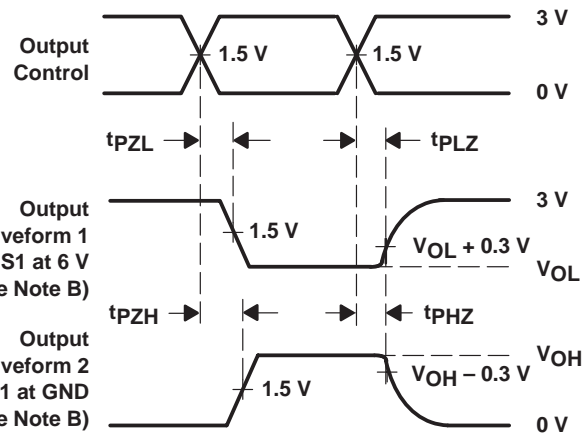
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

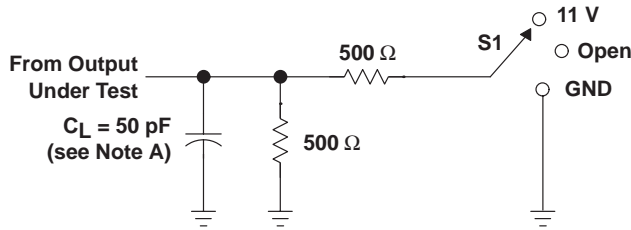
- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

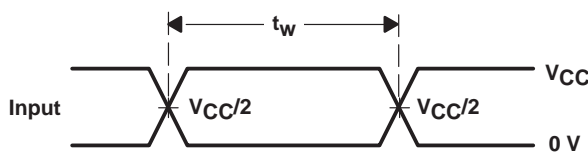
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

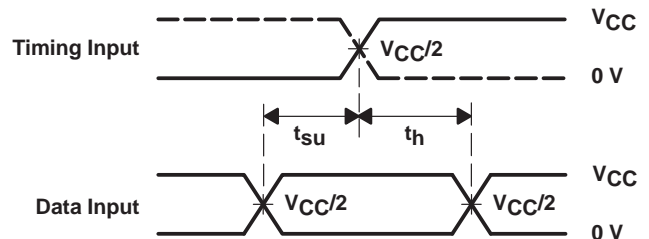


LOAD CIRCUIT

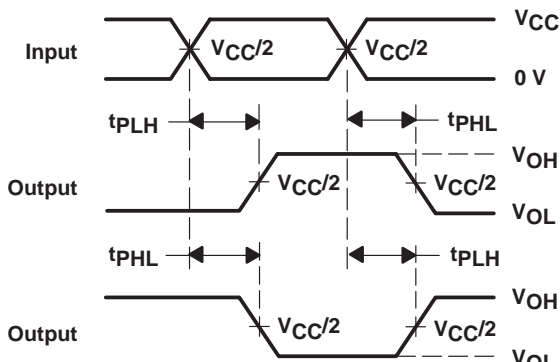
| TEST | S1 |
|-------------------|------|
| t_{PLH}/t_{PHL} | Open |
| t_{PLZ}/t_{PZL} | 11 V |
| t_{PHZ}/t_{PZH} | GND |



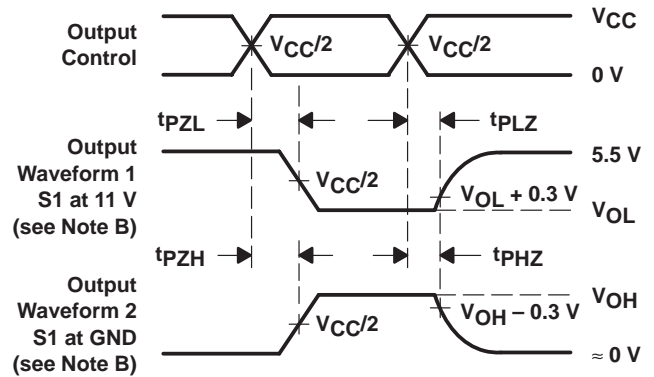
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 4. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

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